

Michael Lw Thewalt

List of Publications by Year in descending order

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78
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254
all docs

254
docs citations

254
times ranked

4632
citing authors

#	ARTICLE	IF	CITATIONS
1	Optical dating of sediments. Nature, 1985, 313, 105-107.	27.8	1,077
2	Isotope effects on the optical spectra of semiconductors. Reviews of Modern Physics, 2005, 77, 1173-1224.	45.6	380
3	Room-Temperature Quantum Bit Storage Exceeding 39 Minutes Using Ionized Donors in Silicon-28. Science, 2013, 342, 830-833.	12.6	341
4	Well-resolved band-edge photoluminescence of excitons confined in strained Si _{1-x} Ge _x quantum wells. Physical Review Letters, 1991, 66, 1362-1365.	7.8	306
5	Quantum Information Storage for over 180 s Using Donor Spins in a ²⁸ Si Semiconductor Vacuum. Science, 2012, 336, 1280-1283.	12.6	269
6	Type II photoluminescence and conduction band offsets of GaAsSb/InGaAs and GaAsSb/InP heterostructures grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 1998, 73, 2799-2801.	3.3	147
7	Reaching the quantum limit of sensitivity in electron spin resonance. Nature Nanotechnology, 2016, 11, 253-257.	31.5	141
8	Type II Band Alignment in Si _{1-x} Ge _x /Si(001) Quantum Wells: The Ubiquitous Type I Luminescence Results from Band Bending. Physical Review Letters, 1997, 79, 269-272.	7.8	114
9	Defect-free band-edge photoluminescence and band gap measurement of pseudomorphic Si _{1-x} Ge _y C _y alloy layers on Si (100). Applied Physics Letters, 1995, 67, 3915-3917.	3.3	109
10	Thermoluminescence spectra of some mineral samples relevant to thermoluminescence dating. Journal of Luminescence, 1988, 39, 123-136.	3.1	100
11	Details of the structure of bound excitons and bound multiexciton complexes in Si. Canadian Journal of Physics, 1977, 55, 1463-1480.	1.1	90
12	High quantum efficiency photoluminescence from localized excitons in Si _{1-x} Ge _x . Applied Physics Letters, 1992, 60, 3174-3176.	3.3	89
13	Theory of formation of phase holograms in lithium niobate. Applied Physics Letters, 1974, 24, 264-265.	3.3	86
14	Photoluminescence studies of the neutralization of acceptors in silicon by atomic hydrogen. Applied Physics Letters, 1985, 46, 689-691.	3.3	80
15	Optical investigation of biexcitons and bound excitons in GaAs quantum wells. Physical Review B, 1988, 38, 3583-3586.	3.2	79
16	Central cell effects on acceptor spectra in Si and Ge. Solid State Communications, 1980, 33, 277-279.	1.9	78
17	Highly structured singlet oxygen photoluminescence from crystalline C ₆₀ . Physical Review Letters, 1992, 69, 2423-2426.	7.8	75
18	Temperature Dependence of the Energy Gap of Semiconductors in the Low-Temperature Limit. Physical Review Letters, 2004, 92, 196403.	7.8	75

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19	Photoluminescence of Isotopically Purified Silicon: How Sharp are Bound Exciton Transitions?. Physical Review Letters, 2001, 86, 6010-6013.	7.8	73
20	Room-temperature 1.3 μ m electroluminescence from strained Si $_{1-x}$ Gex/Si quantum wells. Applied Physics Letters, 1992, 60, 3177-3179.	3.3	70
21	Quantum confinement effects in strained silicon-germanium alloy quantum wells. Applied Physics Letters, 1992, 60, 2135-2137.	3.3	67
22	Impurity Absorption Spectroscopy in Si $_{28}$: The Importance of Inhomogeneous Isotope Broadening. Physical Review Letters, 2003, 90, 186402.	7.8	67
23	Transformation of spatially direct to spatially indirect excitons in coupled double quantum wells. Physical Review B, 1988, 38, 6287-6290.	3.2	64
24	Photoluminescence from electron-hole plasmas confined in Si/Si $_{1-x}$ Gex/Si quantum wells. Applied Physics Letters, 1992, 60, 1720-1722.	3.3	63
25	Optical Detection and Ionization of Donors in Specific Electronic and Nuclear Spin States. Physical Review Letters, 2006, 97, 227401.	7.8	63
26	Fast, low-power manipulation of spin ensembles in superconducting microresonators. Applied Physics Letters, 2014, 104, .	3.3	63
27	Low-temperature photoluminescence of epitaxial InAs. Journal of Applied Physics, 1996, 80, 6416-6424.	2.5	60
28	Exciton luminescence in Si $_{1-x}$ Gex/Si heterostructures grown by molecular beam epitaxy. Journal of Applied Physics, 1993, 74, 2790-2805.	2.5	58
29	Optically detected librions and phonons in crystalline C $_{60}$. Physical Review B, 1993, 48, 11446-11449.	3.2	58
30	A comparison of techniques for nondestructive composition measurements in CdZnTe substrates. Journal of Electronic Materials, 1995, 24, 697-705.	2.2	57
31	Silicon-Integrated Telecommunications Photon-Spin Interface. PRX Quantum, 2020, 1, .	9.2	56
32	InAs/InAsSb strain balanced superlattices for optical detectors: Material properties and energy band simulations. Journal of Applied Physics, 2012, 111, 034507.	2.5	54
33	Effect of neutral donor scattering on the time-dependent exciton-polariton photoluminescence line shape in GaAs. Physical Review B, 1986, 34, 1006-1013.	3.2	53
34	Non-Ohmic Behavior of cis-Polyacetylene Doped with AsF $_5$. Physical Review Letters, 1980, 45, 490-493.	7.8	49
35	Photoluminescence in heavily doped Si: B and Si: As. Solid State Communications, 1981, 38, 1091-1093.	1.9	49
36	Lithium and lithium-carbon isoelectronic complexes in silicon: Luminescence-decay-time, absorption, isotope-splitting, and Zeeman measurements. Physical Review B, 1984, 29, 4517-4523.	3.2	49

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37	Simultaneous Subsecond Hyperpolarization of the Nuclear and Electron Spins of Phosphorus in Silicon by Optical Pumping of Exciton Transitions. <i>Physical Review Letters</i> , 2009, 102, 257401.	7.8	49
38	Strain balanced InAs/InAsSb superlattice structures with optical emission to 10 μ m. <i>Applied Physics Letters</i> , 2009, 95, .	3.3	48
39	Simultaneous subnanosecond timing information and 2D spatial information from imaging photomultiplier tubes. <i>Review of Scientific Instruments</i> , 1987, 58, 1626-1628.	1.3	47
40	Photoluminescence lifetime, absorption and excitation spectroscopy measurements on isoelectronic bound excitons in beryllium-doped silicon. <i>Solid State Communications</i> , 1982, 44, 573-577.	1.9	43
41	Enhancement of long lifetime lines in photoluminescence from Si:In. <i>Solid State Communications</i> , 1981, 39, 27-30.	1.9	41
42	Long lifetime photoluminescence from a deep centre in copper-doped silicon. <i>Solid State Communications</i> , 1982, 43, 687-690.	1.9	41
43	Reduction of the Linewidths of Deep Luminescence Centers in Si ²⁸ Reveals Fingerprints of the Isotope Constituents. <i>Physical Review Letters</i> , 2008, 100, 177402.	7.8	41
44	Photoluminescence of deep defects involving transition metals in Si: New insights from highly enriched ²⁸ Si. <i>Journal of Applied Physics</i> , 2011, 110, .	2.5	41
45	Fine Structure of the Luminescence from Excitons and Multiexciton Complexes Bound to Acceptors in Si. <i>Physical Review Letters</i> , 1977, 38, 521-524.	7.8	40
46	Isoelectronic bound excitons in In- and Tl-doped Si: A novel semiconductor defect. <i>Physical Review B</i> , 1984, 29, 5727-5738.	3.2	40
47	Photoluminescence studies of the EL2 defect in gallium arsenide under external perturbations. <i>Physical Review Letters</i> , 1991, 67, 112-115.	7.8	40
48	Can highly enriched ²⁸ Si reveal new things about old defects?. <i>Physica B: Condensed Matter</i> , 2007, 401-402, 587-592.	2.7	40
49	Shallow impurity absorption spectroscopy in isotopically enriched silicon. <i>Physical Review B</i> , 2009, 79, .	3.2	40
50	Fourier-transform magnetophotoluminescence spectroscopy of donor-bound excitons in GaAs. <i>Physical Review B</i> , 1994, 49, 16381-16397.	3.2	38
51	Photoluminescence studies of isotopically enriched silicon: isotopic effects on the indirect electronic band gap and phonon energies. <i>Solid State Communications</i> , 2002, 123, 87-92.	1.9	38
52	A new photoluminescence band in silicon lightly doped with copper. <i>Solid State Communications</i> , 1988, 68, 7-11.	1.9	36
53	Hyperfine Structure and Nuclear Hyperpolarization Observed in the Bound Exciton Luminescence of Bi Donors in Natural Si. <i>Physical Review Letters</i> , 2010, 104, 137402.	7.8	36
54	Optically-detected NMR of optically-hyperpolarized ³¹ P neutral donors in ²⁸ Si. <i>Journal of Applied Physics</i> , 2011, 109, .	2.5	36

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55	Biexcitons in Si. Solid State Communications, 1978, 25, 991-993.	1.9	35
56	Detailed ground- and excited-state spectroscopy of indirect free excitons. Physical Review Letters, 1988, 61, 1882-1884.	7.8	35
57	Formation of aDXcenter in InP under hydrostatic pressure. Physical Review Letters, 1992, 68, 3619-3622.	7.8	35
58	Photoluminescence mechanisms in thinSi1â ^ˆ xGexquantum wells. Physical Review B, 1993, 47, 16655-16658.	3.2	35
59	Far-Infrared Absorption Spectrum of Be-Related Bound Excitons in Silicon. Physical Review Letters, 1984, 52, 81-84.	7.8	34
60	High-Purity, Isotopically Enriched Bulk Silicon. Journal of the Electrochemical Society, 2005, 152, G448.	2.9	34
61	Direct observation of the donor nuclear spin in a near-gap bound exciton transition: P31 in highly enriched S28i. Journal of Applied Physics, 2007, 101, 081724.	2.5	34
62	Linear Hyperfine Tuning of Donor Spins in Silicon Using Hydrostatic Strain. Physical Review Letters, 2018, 120, 167701.	7.8	34
63	Discovery of Polyexcitons. Physical Review Letters, 1987, 59, 2899-2902.	7.8	33
64	Time-dependent recombination spectra arising from optical ejection of trapped charges in feldspars. Journal of Luminescence, 1989, 44, 41-46.	3.1	33
65	Highly enriched ^{28}Si reveals remarkable optical linewidths and fine structure for well-known damage centers. Physical Review B, 2018, 98, .	3.2	33
66	Growth and band gap of strained ^{110}Si layers on silicon substrates by chemical vapor deposition. Applied Physics Letters, 1994, 65, 76-78.	3.3	32
67	Growth and photoluminescence of high quality SiGeC random alloys on silicon substrates. Journal of Applied Physics, 1996, 80, 3043-3047.	2.5	32
68	Photoluminescence lifetimes of bound excitons in ZnSe. Solid State Communications, 1985, 56, 933-936.	1.9	31
69	Modification of the shapes of GaAs/AlGaAs quantum wells using rapid thermal annealing. Superlattices and Microstructures, 1989, 5, 321-325.	3.1	30
70	Anomalous splitting of the $\text{F}_{1u}(\hat{1}^3\text{F}_u)$ vibrations in single-crystal C60 below the orientational-ordering transition. Physical Review B, 1994, 49, 7052-7055.	3.2	30
71	Intrinsic Acceptor Ground State Splitting in Silicon: An Isotopic Effect. Physical Review Letters, 2002, 89, 016401.	7.8	30
72	Raman Fine Structure in Crystalline C60: The Effects of Merohedral Disorder, Isotopic Substitution, and Crystal Field. Physical Review Letters, 1995, 74, 194-197.	7.8	29

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73	Hybrid optical-electrical detection of donor electron spins with bound excitons in silicon. Nature Materials, 2015, 14, 490-494.	27.5	29
74	Green and near-infrared luminescence due to the biexcitons in unperturbed silicon. Physical Review B, 1984, 30, 6232-6234.	3.2	28
75	EXCITATION ENERGY TRANSFER IN THE CRYPTOPHYTES. FLUORESCENCE EXCITATION SPECTRA AND PICOSECOND TIME-RESOLVED EMISSION SPECTRA OF INTACT ALGAE AT 77 K. Photochemistry and Photobiology, 1986, 44, 519-525.	2.5	28
76	Optical properties of the sulfur-related isoelectronic bound excitons in Si. Physical Review B, 1989, 40, 9618-9625.	3.2	28
77	Effects of sulfur isotopic composition on the band gap of PbS. Physical Review B, 2006, 73, .	3.2	28
78	Observation of a large ground-state splitting in the infrared absorption spectrum of Zn in Ge. Physical Review B, 1985, 32, 2663-2666.	3.2	26
79	Visible photoluminescence from biexcitons in Si _{1-x} Ge _x quantum wells. Solid State Communications, 1994, 89, 429-432.	1.9	26
80	Deep photoluminescence in Si/Si _{1-x} Ge _x /Si quantum wells created by ion implantation and annealing. Applied Physics Letters, 1994, 64, 2291-2293.	3.3	26
81	Sharp excitonic photoluminescence from epitaxial InAs. Applied Physics Letters, 1995, 66, 1101-1103.	3.3	26
82	Raman-scattering study of isotopically engineered crystalline C ₆₀ . Physical Review B, 1996, 54, 920-929.	3.2	26
83	Electrical and optical properties of carbon-doped GaSb. Physical Review B, 2003, 67, .	3.2	25
84	Excited states of donor bound excitons and bound multiexciton complexes in silicon. Solid State Communications, 1977, 21, 937-939.	1.9	24
85	Piezospectroscopic studies of phosphorus-, boron-, and lithium-doped silicon. Canadian Journal of Physics, 1979, 57, 1898-1923.	1.1	24
86	Photoluminescence lifetimes of the In, Tl and Bi bound excitons in silicon. Solid State Communications, 1984, 49, 1121-1123.	1.9	24
87	Pressured-Induced Structural Metastability in Crystalline C ₆₀ . Physical Review Letters, 1995, 74, 3483-3486.	7.8	24
88	Origin of the Residual Acceptor Ground-State Splitting in Silicon. Physical Review Letters, 2003, 90, 016404.	7.8	24
89	High-resolution absorption spectroscopy of the deep impurities S and Se in silicon. Physical Review Letters, 2003, 90, 016404.	3.2	24
90	Electron paramagnetic resonance of boron acceptors in isotopically purified silicon. Physical Review B, 2010, 81, .	3.2	24

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91	¹³ C hyperfine coupling constants in MuC60. Chemical Physics Letters, 1995, 245, 90-94.	2.6	23
92	Isotope effect on electron paramagnetic resonance of boron acceptors in silicon. Physical Review B, 2010, 82, .	3.2	23
93	Comments on "experimental evidence against the shell model of bound multiexciton complexes in silicon", Solid State Communications, 1978, 25, 513-517.	1.9	22
94	Phonon broadening of bound exciton luminescence in silicon. Canadian Journal of Physics, 1976, 54, 1728-1740.	1.1	21
95	Photoluminescence study of nitrogen-oxygen donors in silicon. Applied Physics Letters, 1990, 56, 148-150.	3.3	21
96	High Temperature (77-300 K) Photo- and Electroluminescence in Si/Si _{1-x} Ge _x Heterostructures. Japanese Journal of Applied Physics, 1994, 33, 2329-2334.	1.5	21
97	Enhancement of high-temperature photoluminescence in strained Si _{1-x} Ge _x /Si heterostructures by surface passivation. Applied Physics Letters, 1994, 65, 3344-3346.	3.3	21
98	Thermal-Donor-Related Isoelectronic Center in Silicon Which Can Bind up to Four Excitons. Physical Review Letters, 1986, 57, 1939-1942.	7.8	20
99	Nearly ideal InP/GaAsSb/InP double heterojunction bipolar transistors with ballistically launched collector electrons. Electronics Letters, 1998, 34, 1700.	1.0	20
100	Dependence of the ionization energy of shallow donors and acceptors in silicon on the host isotopic mass. Physical Review B, 2003, 68, .	3.2	20
101	Isoelectronic bound excitons in silicon: The role of deep acceptors. Physical Review B, 1981, 24, 3655-3658.	3.2	19
102	Photoluminescence transitions of the deep EL2 defect in gallium arsenide. Physical Review Letters, 1990, 65, 2282-2285.	7.8	19
103	Even-parity acceptor excited states in Si from bound exciton two hole transitions. Solid State Communications, 1977, 23, 733-735.	1.9	18
104	Time-resolved photoluminescence study of InSe. Solid State Communications, 1985, 56, 929-931.	1.9	18
105	The far infrared absorption spectra of bound excitons in silicon. Solid State Communications, 1985, 53, 1049-1054.	1.9	18
106	Magnetophotoluminescence characterization of residual donors in GaAs grown by metalorganic chemical vapor deposition. Journal of Applied Physics, 1988, 64, 3205-3209.	2.5	18
107	Large photoluminescence enhancements from epitaxial GaAs passivated by postgrowth phosphidization. Applied Physics Letters, 1997, 70, 3275-3277.	3.3	18
108	Photoluminescence studies of isoelectronic bound excitons associated with the deep acceptors In and Tl in Si. Canadian Journal of Physics, 1982, 60, 1691-1708.	1.1	17

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109	Photoluminescence of excitons bound to the isoelectronic hydrogen-related defects B711 (1.1377 eV) in silicon. <i>Physical Review B</i> , 1994, 50, 7338-7343.	3.2	17
110	P-type carbon doping of GaSb. <i>Journal of Electronic Materials</i> , 2001, 30, 1429-1432.	2.2	17
111	Spectroscopy of excitons and shallow impurities in isotopically enriched silicon's electronic properties beyond the virtual crystal approximation. <i>Solid State Communications</i> , 2005, 133, 715-725.	1.9	17
112	Optical pumping and readout of bismuth hyperfine states in silicon for atomic clock applications. <i>Scientific Reports</i> , 2015, 5, 10493.	3.3	16
113	Characterization of the $\text{Si}^{+}\text{Se}^{-}$ spin-photon interface. <i>Physical Review Applied</i> , 2019, 11, .	3.8	16
114	Photoluminescence studies of bound multiexciton complexes associated with Li in Si. <i>Solid State Communications</i> , 1978, 28, 361-364.	1.9	15
115	Disappearance of Be-related photoluminescence in Be-doped Ge under large uniaxial stresses. <i>Solid State Communications</i> , 1985, 54, 1043-1046.	1.9	15
116	Ultrahigh-resolution photoluminescence studies of excitons bound to boron in silicon under uniaxial stress. <i>Physical Review B</i> , 1992, 45, 11736-11743.	3.2	15
117	Photoluminescence spectroscopy of localized excitons in $\text{Si}_{1-x}\text{Ge}_x$. <i>Journal of Electronic Materials</i> , 1993, 22, 233-238.	2.2	15
118	Intrinsic Splitting of the Acceptor Ground State in Silicon. <i>Physical Review Letters</i> , 1994, 73, 2340-2343.	7.8	15
119	Fourier Transform Raman and Brillouin Spectroscopy Using Atomic Vapor Filters. <i>Applied Spectroscopy</i> , 1994, 48, 843-847.	2.2	15
120	Inductive Measurement of Optically Hyperpolarized Phosphorous Donor Nuclei in an Isotopically Enriched Silicon-28 Crystal. <i>Physical Review Letters</i> , 2014, 113, 267604.	7.8	15
121	Optical properties of shallow defect-related acceptors in GaAs grown by molecular-beam epitaxy. <i>Physical Review B</i> , 1990, 41, 8221-8228.	3.2	14
122	Method for shallow impurity characterization in ultrapure silicon using photoluminescence. <i>Journal of Applied Physics</i> , 2002, 92, 5913-5916.	2.5	14
123	High resolution photoluminescence of sulphur- and copper-related isoelectronic bound excitons in highly enriched ^{28}Si . <i>Physica B: Condensed Matter</i> , 2007, 401-402, 593-596.	2.7	14
124	Far-infrared absorption spectra of the ground-state to excited-state transitions of excitons bound to the double acceptors Be and Zn in Ge. <i>Physical Review B</i> , 1985, 32, 5514-5516.	3.2	13
125	Time-resolved photoluminescence study of molecular beam epitaxial growth induced defect lines in GaAs. <i>Applied Physics Letters</i> , 1985, 47, 257-259.	3.3	13
126	Use of polypropylene film for infrared cryogenic windows. <i>Applied Optics</i> , 1986, 25, 171.	2.1	13

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127	Photoluminescence studies of ultrahigh-purity epitaxial silicon. Applied Physics Letters, 1986, 49, 1444-1446.	3.3	13
128	Optical techniques for characterizing Si GaAs. Canadian Journal of Physics, 1989, 67, 242-250.	1.1	13
129	Observation of luminescence from the EL2 metastable state in liquid-encapsulated Czochralski-grown GaAs under hydrostatic pressure. Physical Review B, 1993, 47, 1265-1269.	3.2	13
130	Disorder, impurity, and isotope effects in the Raman-active libron spectrum of crystalline C60. Physical Review B, 1995, 52, R6951-R6954.	3.2	13
131	Homogeneous linewidth of the P31 bound exciton transition in silicon. Applied Physics Letters, 2009, 95, .	3.3	13
132	Sharp-line, donor-acceptor pair recombination luminescence in Si(In,Li), Si(Ga,Li), Si(Al,Li), and Si(B,Li). Canadian Journal of Physics, 1982, 60, 1041-1052.	1.1	12
133	A zinc-related isoelectronic bound exciton in silicon. Solid State Communications, 1988, 66, 689-694.	1.9	12
134	Time-resolved studies of biexcitons in GaAs. Solid State Communications, 1989, 69, 1139-1142.	1.9	12
135	Time-dependent recombination luminescence spectra arising from optical ejection of trapped charges in zircons. Journal of Luminescence, 1989, 44, 47-57.	3.1	12
136	Local vibrational mode study of carbon-doped InAs. Physical Review B, 2006, 74, .	3.2	12
137	Effects of Uniaxial Stress on the Luminescence Lines Due to Multiexciton Complexes Bound to Phosphorus in Silicon. Physical Review Letters, 1978, 41, 808-812.	7.8	11
138	Resonant photoluminescence studies of the growth-induced defects in GaAs grown by molecular beam epitaxy. Physical Review B, 1988, 38, 3587-3590.	3.2	11
139	Enhancement of luminescence in GaAs by low levels of Cu. Applied Physics Letters, 1991, 58, 714-716.	3.3	11
140	In-situ monitoring, structural, and optical properties of ultrathin GaSb/GaAs quantum wells grown by OMVPE. Journal of Electronic Materials, 2001, 30, 1412-1416.	2.2	11
141	Effect of the isotopic mass of gallium on the indirect gap of GaP. Solid State Communications, 2003, 126, 119-123.	1.9	11
142	Raman scattering in carbon-doped InAs. Applied Physics Letters, 2006, 88, 041908.	3.3	11
143	Impurity absorption spectroscopy of the deep double donor sulfur in isotopically enriched silicon. Physica B: Condensed Matter, 2007, 401-402, 600-603.	2.7	11
144	Further investigations of the deep double donor magnesium in silicon. Physical Review B, 2018, 98, .	3.2	11

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145	Photoluminescence studies of defects in annealed Czochralski silicon. Canadian Journal of Physics, 1989, 67, 268-274.	1.1	10
146	Band-edge exciton luminescence from Si/strained Si _{1-x} Ge _x /Si structures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 1998.	1.6	10
147	Characterization of very high purity InAs grown using trimethylindium and tertiarybutylarsine. Journal of Electronic Materials, 1995, 24, 1583-1590.	2.2	10
148	Fourier-transform photoluminescence spectroscopy of excitons bound to group-III acceptors in silicon: Zeeman effect. Physical Review B, 1996, 54, 10543-10558.	3.2	10
149	Effect of Bi surfactant on atomic ordering of GaAsSb. Applied Physics Letters, 2004, 85, 5589-5591.	3.3	10
150	Sulfur isotope effects on the excitonic spectra of CdS. Physical Review B, 2004, 69, .	3.2	10
151	Isotopic fingerprints of Pt-containing luminescence centers in highly enriched S ²⁸ . Physical Review B, 2010, 81, .	3.2	10
152	Direct observation of the ground state splitting of the indirect free exciton in silicon. Solid State Communications, 1976, 20, 97-99.	1.9	9
153	Transient response of superconducting Pb microbridges irradiated by picosecond laser pulses and its potential applications. IEEE Transactions on Magnetics, 1981, 17, 88-91.	2.1	9
154	Photoluminescence studies of Si implanted with In and/or Tl: The effects of thermal treatment and atomic H. Journal of Applied Physics, 1985, 57, 498-502.	2.5	9
155	A second isoelectronic multiexciton center in annealed Czochralski silicon. Solid State Communications, 1987, 63, 81-84.	1.9	9
156	Piezospectroscopy of the ground and excited states of zinc double acceptors in germanium. Physical Review B, 1988, 38, 5504-5510.	3.2	9
157	Photoluminescence from excitons bound to a triple acceptor, Ge:Cu. Physical Review B, 1990, 41, 7926-7928.	3.2	9
158	Photoluminescence decay times of the defect-induced bound-exciton lines in GaAs grown by molecular-beam epitaxy. Physical Review B, 1990, 41, 2861-2864.	3.2	9
159	Zero-field optical magnetic resonance study of phosphorus donors in ²⁸ -silicon. Physical Review B, 2018, 97, .	3.2	9
160	Shallow donor complexes formed by pairing of double-donor magnesium with group-III acceptors in silicon. Physical Review B, 2019, 99, .	3.2	9
161	Radio frequency dielectric dissipation measurements on yttrium oxide thin films. Thin Solid Films, 1972, 13, 195-198.	1.8	8
162	Donor-acceptor pair luminescence in Si(In,Li): Observation of the In center. Applied Physics Letters, 1981, 39, 972-974.	3.3	8

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163	Photoluminescence and infrared absorption studies of Ge doped with Mg. Solid State Communications, 1985, 56, 751-754.	1.9	8
164	Excitation spectroscopy of the In-related isoelectronic bound exciton under uniaxial stress and magnetic-field perturbations. Physical Review B, 1986, 34, 2598-2605.	3.2	8
165	Stereochemical controls on exciplex reactions. Excited state proton transfer. Journal of the American Chemical Society, 1988, 110, 5543-5547.	13.7	8
166	Photoluminescence for characterization of commercial semi-insulating GaAs. Canadian Journal of Physics, 1989, 67, 384-388.	1.1	8
167	Double fluorescence lifetimes of metal-free phthalocyanine in a mixed-solvent Shpol'skii matrix at 4Å ² K. Molecular Physics, 1989, 67, 1439-1443.	1.7	8
168	Quantitative, all-optical prediction of the carrier density in semi-insulating GaAs. Applied Physics Letters, 1990, 56, 647-649.	3.3	8
169	Splitting of the ground state of shallow acceptors in silicon. Solid State Communications, 1995, 93, 379-382.	1.9	8
170	The pressure dependence of Raman active libron modes in crystalline C60. Solid State Communications, 1995, 93, 575-578.	1.9	8
171	Photoluminescence studies of isotopically enriched silicon. Physica Status Solidi (B): Basic Research, 2003, 235, 63-74.	1.5	8
172	Electrical and optical characterization of n-InAsSb/n-GaSb heterojunctions. Journal of Applied Physics, 2010, 107, 014512.	2.5	8
173	Quantum Hall charge sensor for single-donor nuclear spin detection in silicon. New Journal of Physics, 2010, 12, 093028.	2.9	8
174	Host isotope mass effects on the hyperfine interaction of group-V donors in silicon. Physical Review B, 2014, 90, .	3.2	8
175	Even-parity excited states of the acceptor boron in silicon revisited. Physical Review B, 2016, 93, .	3.2	8
176	Radiative recombination in highly excited ZnSe. Solid State Communications, 1988, 67, 187-191.	1.9	7
177	Evidence for asymmetric well shapes in post-growth modified GaAs/AlGaAs quantum wells. Journal of Applied Physics, 1989, 66, 5532-5535.	2.5	7
178	A photoluminescence study of zinc-implanted silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1989, 4, 201-204.	3.5	7
179	High Performance Photoluminescence Spectroscopy using Fourier Transform Interferometry. Materials Research Society Symposia Proceedings, 1989, 163, 221.	0.1	7
180	Photoluminescence study of vertical transport in Si _{1-x} Gex/Si heterostructures. Physical Review B, 1993, 47, 16659-16662.	3.2	7

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